

Silicon PNP Power Transistors

2SA1718

DESCRIPTION

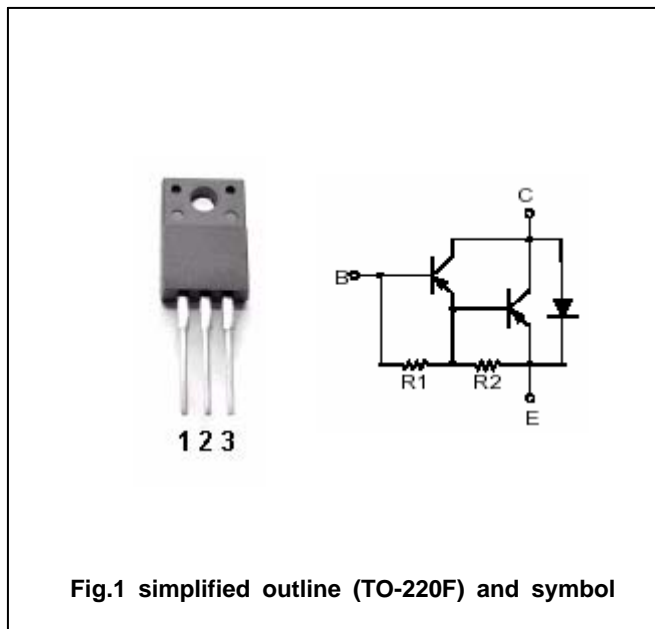
- With TO-220F package
- High DC current gain.
- Low collector saturation voltage.
- DARLINGTON

APPLICATIONS

- Ideal for motor drivers and solenoid drivers application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-5	A
I _{CM}	Collector current-peak		-10	A
I _B	Base current		-0.5	A
P _C	Collector dissipation	T _C =25°C	20	W
		T _a =25°C	2.0	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-30\text{mA}; I_B=0$	-100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2\text{A}; I_B=-2\text{mA}$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2\text{A}; I_B=-2\text{mA}$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-100\text{V}; I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-7\text{V}; I_C=0$			-5.0	mA
h_{FE-1}	DC current gain	$I_C=-2\text{A}; V_{CE}=-2\text{V}$	2000		20000	
h_{FE-2}	DC current gain	$I_C=-4\text{A}; V_{CE}=-2\text{V}$	500			

◆ h_{FE} classifications

M	L	K
2000-5000	4000-10000	8000-20000

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PACKAGE OUTLINE

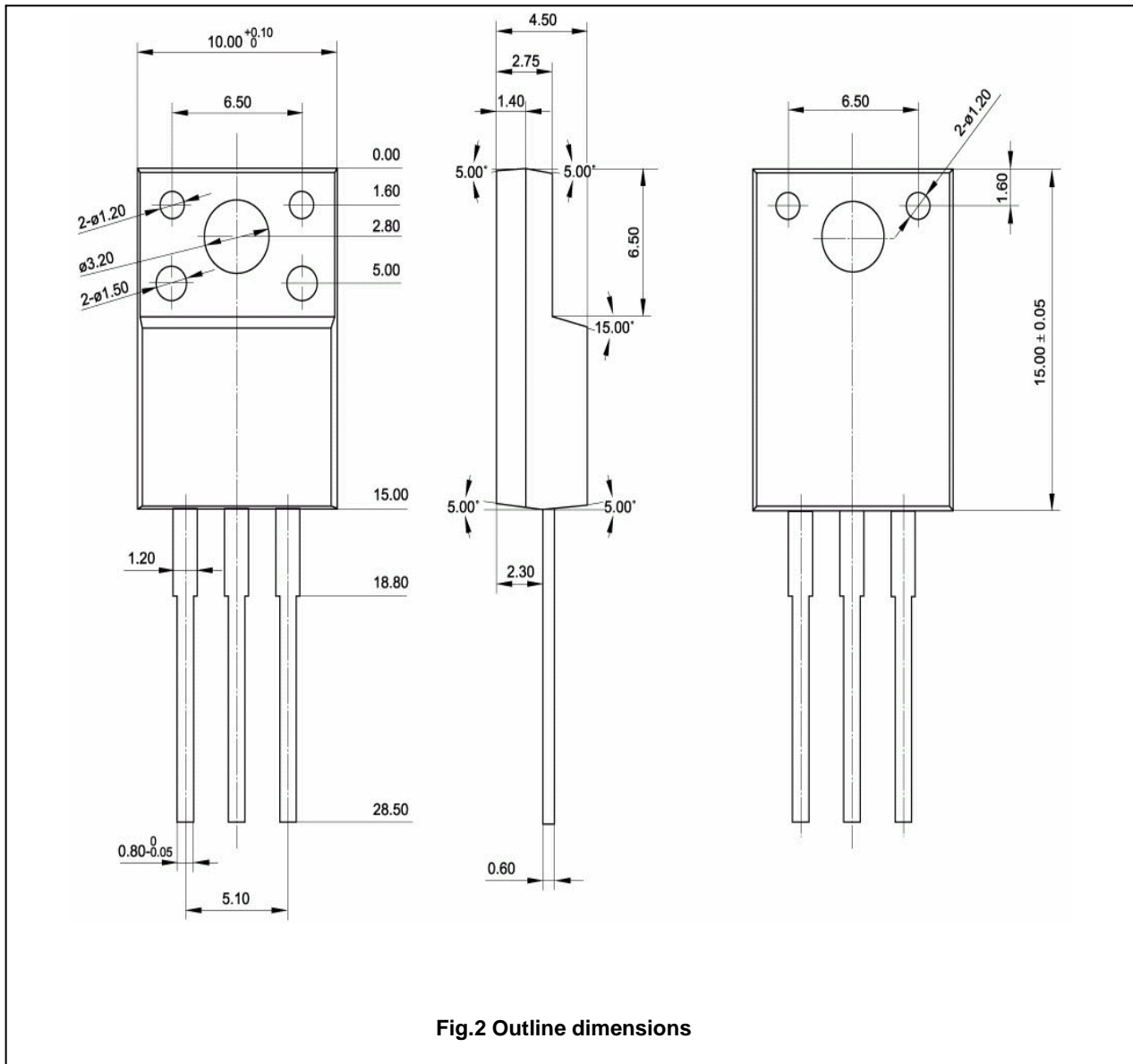


Fig.2 Outline dimensions